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APPLICATION NO.	FILIN	NG DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/052,234	234 01/16/2002		Duc Chau	40013.003	9589
27966	7590	04/20/2005		EXAMINER	
KENNETH KIRTON &			GARCIA, JOANNIE A		
60 EAST SC		_	ART UNIT	PAPER NUMBER	
SUITE 1800			2823		
SALTLAKE CITY, UT 84111				DATE MAILED: 04/20/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
Office Action Summan	10/052,234	CHAU ET AL.	
Office Action Summary	Examiner	Art Unit	(M
	Joannie A. García	2823	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the o	correspondence add	ress
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	mely filed ys will be considered timely. the mailing date of this con ED (35 U.S.C. § 133).	nmunication.
Status			
1) Responsive to communication(s) filed on 03 M	arch 2005.		
2a) ☐ This action is FINAL . 2b) ☒ This	action is non-final.		
3) Since this application is in condition for allowar	nce except for formal matters, pr	osecution as to the	merits is
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.	
Disposition of Claims			
4)⊠ Claim(s) <u>1-17 and 21-24</u> is/are pending in the a	application.		
4a) Of the above claim(s) is/are withdraw			
5) Claim(s) <u>7-17 and 22-24</u> is/are allowed.			
6)⊠ Claim(s) <u>1-6 and 21</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/or	r election requirement.		
Application Papers			
9) The specification is objected to by the Examine	r.		
10) The drawing(s) filed on is/are: a) acce	epted or b) objected to by the	Examiner.	
Applicant may not request that any objection to the	drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the correct		-	
11)☐ The oath or declaration is objected to by the Ex	aminer. Note the attached Office	e Action or form PTC	D-152.
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a	a)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:			
1. Certified copies of the priority documents	s have been received.		
2. Certified copies of the priority documents	• •		
3. Copies of the certified copies of the prior	·	ed in this National S	Stage
application from the International Bureau	* **		
* See the attached detailed Office action for a list	of the certified copies not receive	ea.	
Attachment(c)			
Attachment(s) Notice of References Cited (PTO-892)	4) 🔲 Interview Summary	v (PTO-413)	
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail D	ate	450)
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date <u>03-03-05</u> .	5) Notice of Informal I	Patent Application (PTO-	152)
5. Patent and Trademark Office	-,		

Art Unit: 2823

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-6 are rejected under 35 U.S.C. 102(b) as being anticipated by Nakamura et al (U.S. Patent 5,508,534).

Nakamura et al discloses providing a semiconductor substrate 4 with an upper surface, the substrate having trench 13 therein (Figure 2, and Column 11, lines 33-38), providing a gate oxide layer 14 on a bottom and sidewall of the trench (Figure 2, and Column 11, lines 39-44), providing a conductive layer 5, such as polysilicon, on a bottom and sidewall of the gate oxide layer (Figure 2), the conductive layer having an upper surface below the upper surface of the substrate (Figure 2), providing a self-aligned isolation cap 12/10 on the conductive layer within the trench, the isolation cap comprising a combination of dielectric materials with different etching rates, or a non-organic dielectric material, such as silicon oxide and BPSG, including providing the self-aligned isolation cap by providing a first dielectric layer 12, providing a second dielectric layer 10 over the first dielectric layer, flowing and reflowing the second dielectric layer, and then anisotropically etching the first and second dielectric layers until the upper substrate surface is exposed (Figures 8 and 9, and Column 13, lines 23-32, and 50-67).

Claim 21 is rejected under 35 U.S.C. 102(b) as being anticipated by Nishihara (5,541,425).

Nishihara discloses providing a semiconductor substrate 3 with an upper surface, the substrate having a trench therein (Figure 3), providing source and channel regions proximate the trench (Figure 3, Column 11, lines 5-8, Column 23, lines 42-44, and 55-58, and Column 24, lines 1-2), providing a gate oxide layer 7 on a bottom and sidewall of the trench (Figure 3), providing a conductive layer 8 on a bottom and sidewall of the gate oxide layer (Figure 3), the conductive layer having an upper surface below the upper surface of the substrate (Figure 3), providing a self-aligned isolation cap 9 on the conductive layer within the trench, the isolation cap comprising a non-organic dielectric material (Figure 3, and Column 10, lines 62-67).

Claims 7-17, and 22-24, are allowed.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Joannie García whose telephone number is (571) 272-1861. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (571) 272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

Art Unit: 2823

applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

George Fourson
Primary Examiner
Art Unit 2823

JAG April 14, 2005

GFourson Primary Examiner